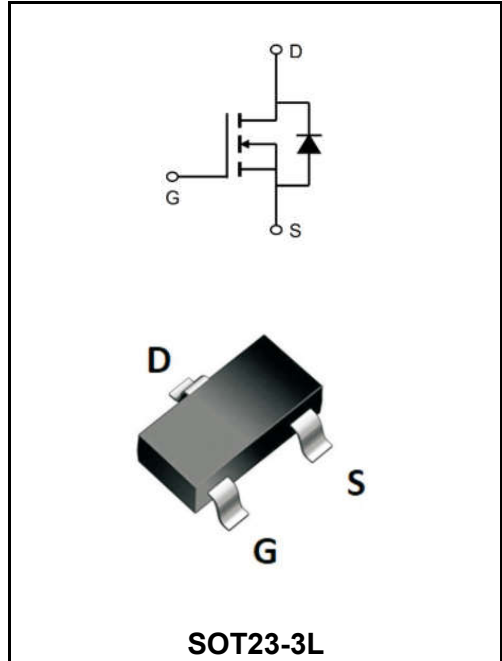


**40V N-CHANNEL ENHANCEMENT MODE MOSFET**

**MAIN CHARACTERISTICS**

<b>I<sub>D</sub></b>	5.0A
<b>V<sub>DSS</sub></b>	40V
<b>R<sub>DS(on)-typ(@V<sub>GS</sub>=10V)</sub></b>	< 37mΩ ( <b>Type:30 mΩ</b> )



**Application**

- ◆ Battery protection
- ◆ Load switch
- ◆ Uninterruptible power supply

<b>Marking Code</b>	
YFW5N04MI	MD4-5A

**Maximum Ratings at T<sub>c</sub>=25°C unless otherwise specified**

Characteristics	Symbols	Value	Units
Drain-Source Voltage	<b>V<sub>DS</sub></b>	40	<b>V</b>
Gate - Source Voltage	<b>V<sub>GS</sub></b>	±20	<b>V</b>
Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup> @T <sub>A</sub> =25°C	<b>I<sub>D</sub></b>	5.0	<b>A</b>
Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup> @T <sub>A</sub> =100°C	<b>I<sub>D</sub></b>	3.5	<b>A</b>
Pulsed Drain Current <sup>2</sup>	<b>I<sub>DM</sub></b>	14	<b>A</b>
Total Power Dissipation <sup>4</sup> @T <sub>A</sub> =25°C	<b>P<sub>D</sub></b>	1	<b>W</b>
Storage Temperature Range	<b>T<sub>STG</sub></b>	-55 to +150	<b>°C</b>
Operating Junction Temperature Range	<b>T<sub>J</sub></b>	-55 to +150	<b>°C</b>
Thermal Resistance Junction-ambient <sup>1</sup>	<b>R<sub>θJA</sub></b>	125	<b>°C/W</b>
Thermal Resistance Junction-Case <sup>1</sup>	<b>R<sub>θJC</sub></b>	80	<b>°C/W</b>

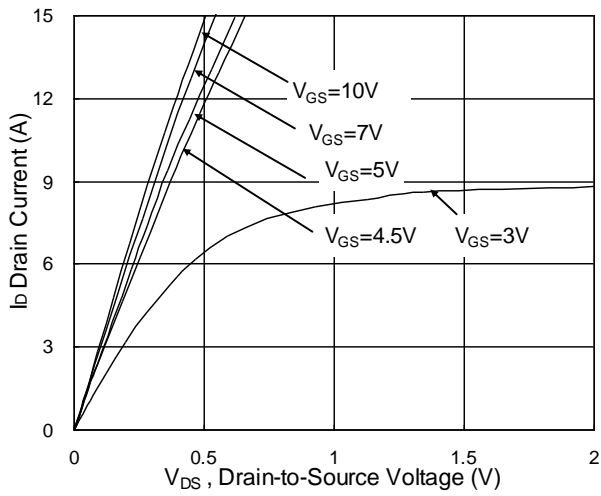
**Maximum Ratings at Tc=25°C unless otherwise specified**

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	$BV_{DSS}$	40	-	-	V
BVDSS Temperature Coefficient	Reference to 25°C, $I_D=1mA$	$\Delta BV_{DSS}/\Delta T_J$	-	0.032	-	V/°C
Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=4A$	$R_{DS(ON)}$	-	30	37	mΩ
	$V_{GS}=4.5V, I_D=3A$		-	40	50	
Gate -Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	$V_{GS(th)}$	1.0	1.5	2.5	V
$V_{GS(th)}$ Temperature Coefficient		$\Delta V_{GS(th)}$	-	-4.5	-	mV/°C
Drain-Source Leakage Current	$V_{DS}=32V, V_{GS}=0V, T_J=25^\circ C$	$I_{DSS}$	-	-	1	μA
	$V_{DS}=32V, V_{GS}=0V, T_J=55^\circ C$		-	-	5	
Gate -Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	$I_{GSS}$	-	-	±100	nA
Forward Transconductance	$V_{DS}=5V, I_D=4A$	$g_{fs}$	-	8	-	S
Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	$R_g$	-	2.4	4.8	Ω
Total Gate Charge(4.5V)	$V_{DS}=15V$ $V_{GS}=4.5V$ $I_D=3A$	$Q_g$	-	5	-	nC
Gate-Source Charge		$Q_{gs}$	-	1.54	-	
Gate-Drain Charge		$Q_{gd}$	-	1.84	-	
Turn-on delay time	$V_{DD}=15V$ $V_{GS}=10V$ $R_G=3.3$ $I_D=1A$	$t_{d(on)}$	-	7.8	-	ns
Rise Time		$T_r$	-	2.1	-	
Turn-Off Delay Time		$t_{d(OFF)}$	-	29	-	
Fall Time		$t_f$	-	2.1	-	
Input Capacitance	$V_{DS}=15V$ $V_{GS}=0V$ $f=1.0MHz$	$C_{iss}$	-	452	-	pF
Output Capacitance		$C_{oss}$	-	51	-	
Reverse Transfer Capacitance		$C_{rss}$	-	38	-	
Continuous Source Current <sup>1,4</sup>	$V_G=V_D=0V, \text{Force Current}$	$I_S$	-	-	4.5	A
Pulsed Source Current <sup>2,4</sup>		$I_{SM}$	-	-	14	A
Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	$V_{SD}$	-	-	1.2	V

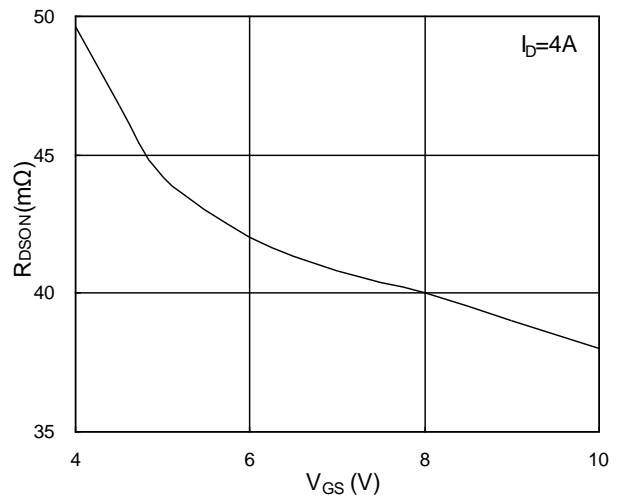
Note :

- 1 .The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\cong 300\mu s$  , duty cycle  $\cong 2\%$
- 3 .The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

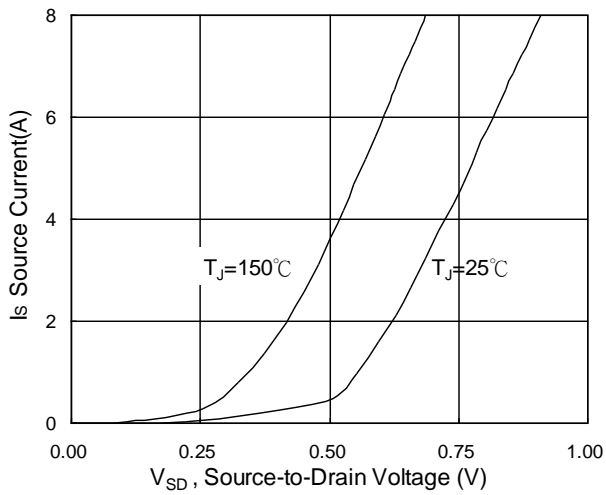
**Ratings and Characteristic Curves**



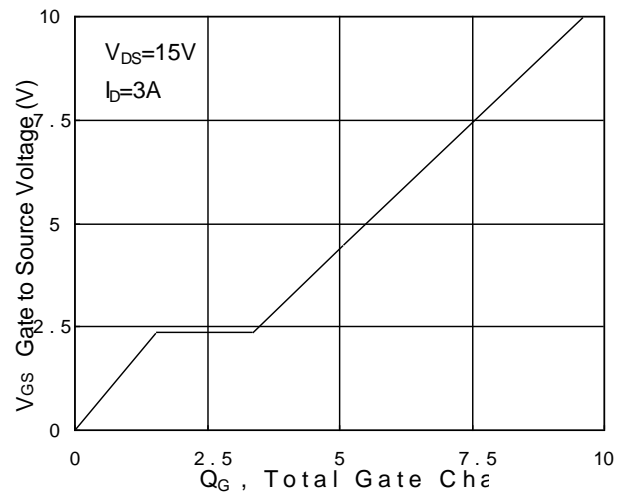
**Fig.1 Typical Output Characteristics**



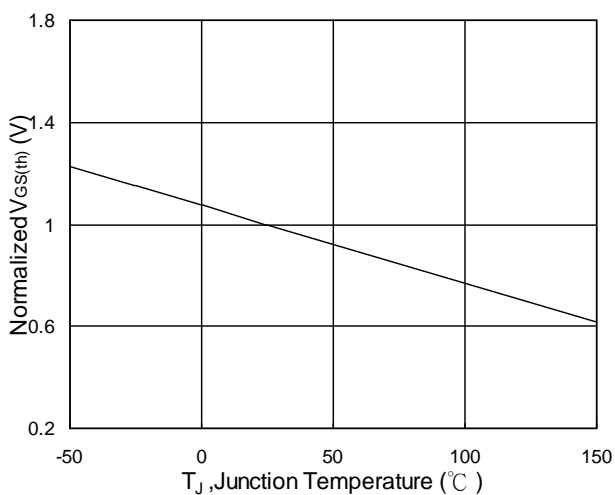
**Fig.2 On-Resistance vs. Gate-Source**



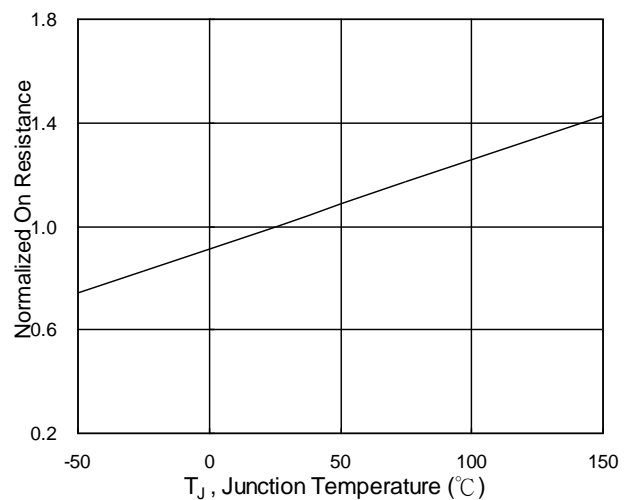
**Fig.3 Forward Characteristics Of Reverse**



**Fig.4 Gate-Charge Characteristics**

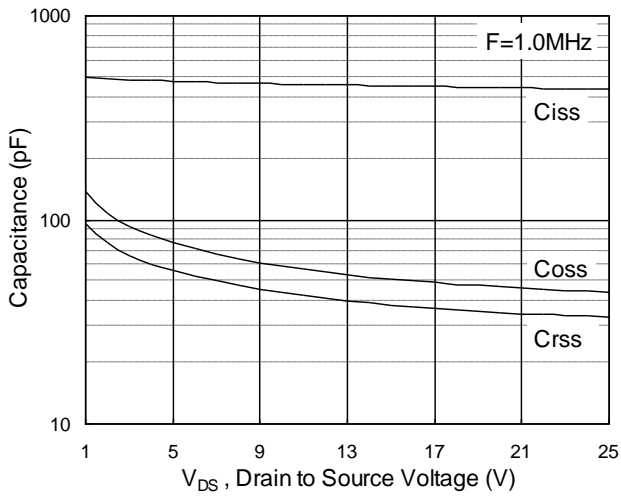


**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**

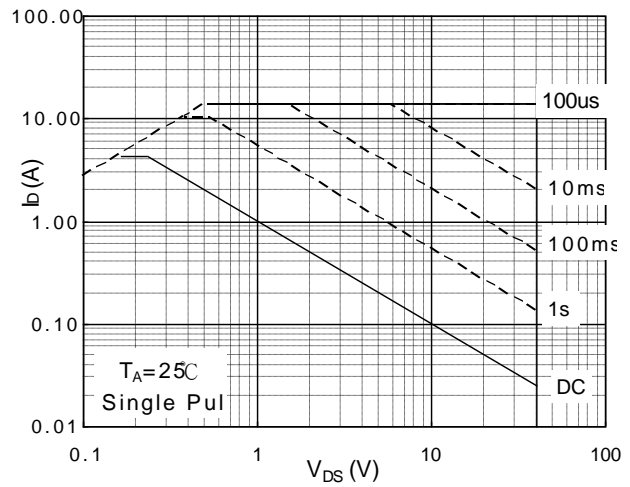


**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**

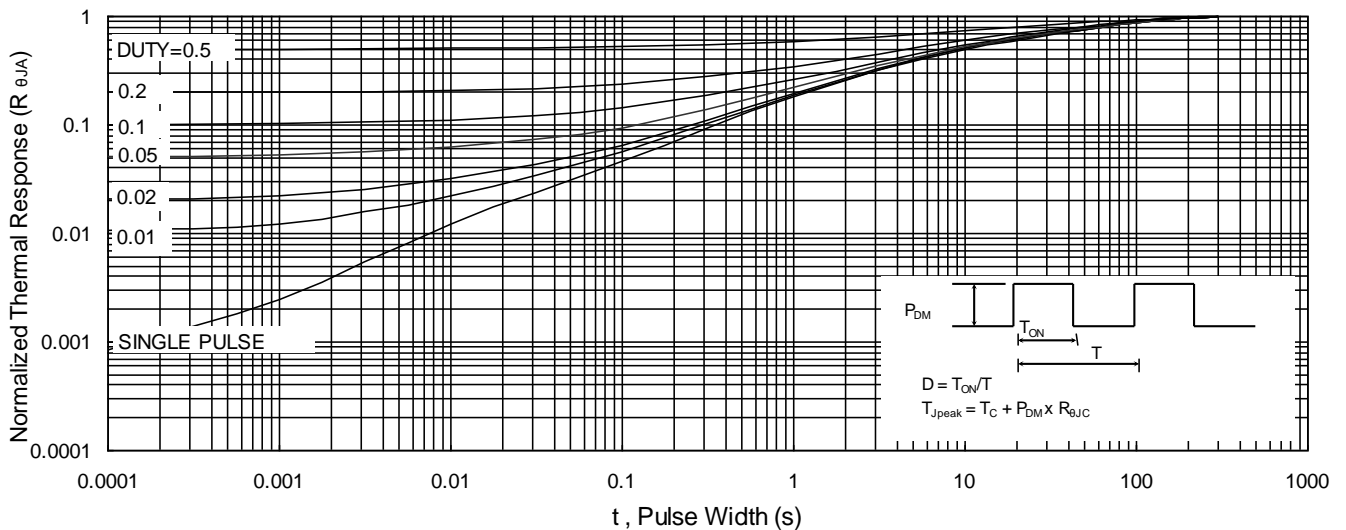
**Ratings and Characteristic Curves**



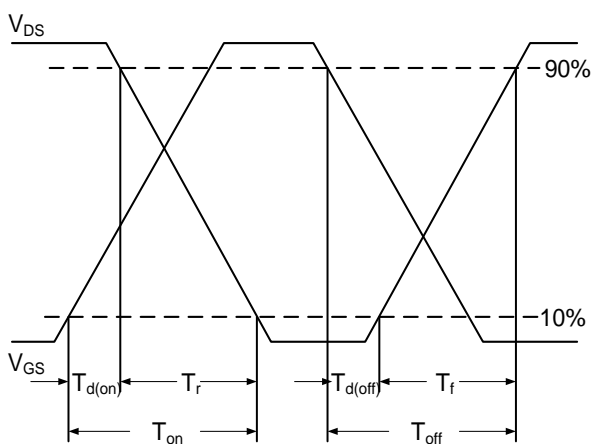
**Fig.7 Capacitance**



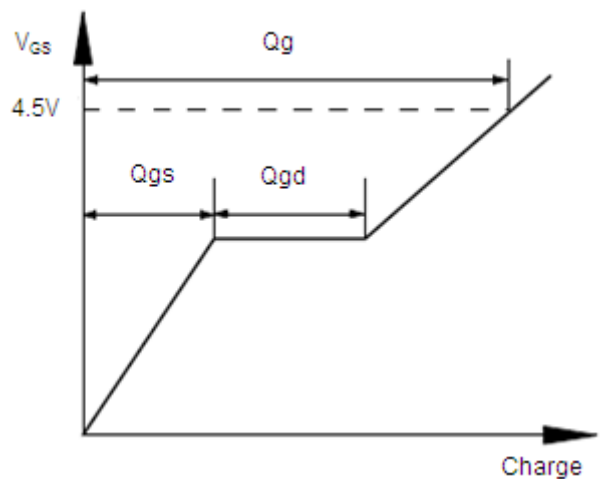
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Gate Charge Waveform**

**Ordering information**

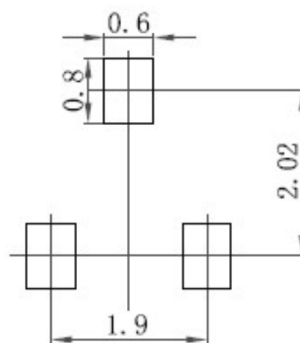
Package	Packing Description	Base Quantity	Packing Quantity
SOT23-3L	Tape/Reel, 7" reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

**Package Dimensions**

**SOT23-3L**

Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
A	1.05	1.25	41	49.2
A1	0.10		3.93	
A2	1.05	1.15	41	45
b	0.30	0.50	12	20
c	0.10	0.20	3.93	7.9
D	2.82	3.02	111	119
E	1.50	1.70	59	67
E1	2.65	2.95	104	116
e	0.95		37.4	
e1	1.80	2.00	71	78
L	0.30	0.066	12	26
Θ	8°			

**The recommended mounting pad size**



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